



TVR30

HIGH VOLTAGE FAST RECOVERY SILICON DIODE FOR CRT APPLICATIONS TYPE - TVR30



This high voltage fast recovery diode was developed for assembly or encapsulation and is intended primarily for use as a building block in the assembly of high voltage circuits for black / white TV and similar service.

ABSOLUTE MAXIMUM RATINGS

Peak Reverse Voltage - Repetitive	V_{RWM} max.	30,000 Volts
* Average Forward Current	$I_{F(AV)}$ max.	10 mA
* Peak Forward Current - Repetitive	I_{FRM} max.	200 mA
** Operating Temperature	T_A	+100 °C
Storage Temperature Range	T_{STG}	-55 °C to +150 °C

*Pulse rectifier service -TV deflection system, duty cycle approximately 15% of one horizontal cycle. Approximately 10 μ sec at a repetition rate of 15,750 Hz

**See Figure 2(over)

ELECTRICAL CHARACTERISTICS (@ $T_A=25^\circ\text{C}$, Unless Otherwise indicated.)

Forward Voltage $V_F @ I_F = 5 \text{ mA}$	45V max.
* Reverse Current $I_R @ V_R = 30\text{KV}$	1uA max.
* Reverse Current @ $T_A = 100^\circ\text{C}$, $I_R @ V_R = 30\text{KV}$	10uA max.
Reverse Recovery time (Fig.3) t_{rr}	100 nanosec max.
Max. Surge Current	3A

* Tested in suitable dielectric medium

EDI reserves the right to change these specifications at any time without notice.

FIG.1 TYPICAL APPLIED VOLTAGE

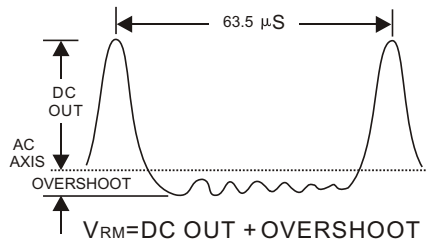


FIG.2 TYPICAL OPERATING CIRCUIT

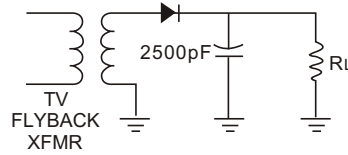
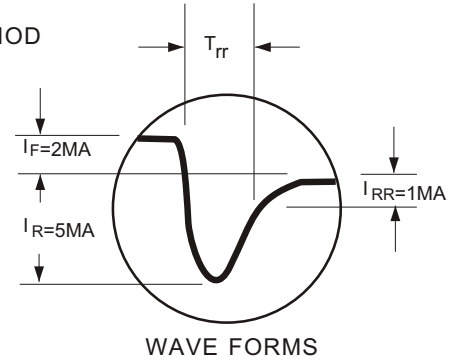
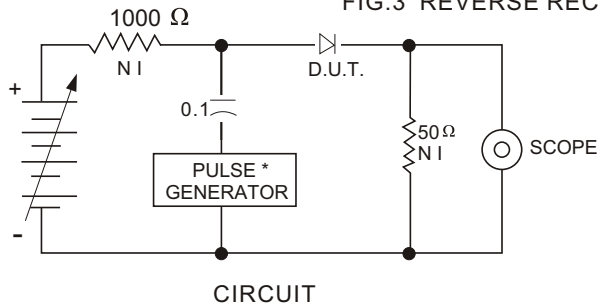
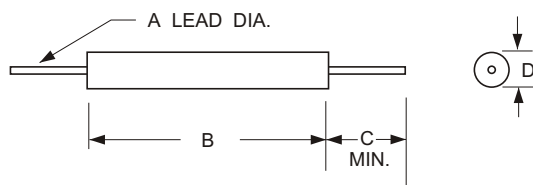


FIG.3 REVERSE RECOVERY TEST METHOD



*PULSE GENERATOR
HP 214 A OR EQUIV.
PULSE WIDTH 1 μS
REP.RATE 10 HKZ

FIG.4 MECHANICAL OUTLINE



	INCHES	MM
A	.020	0.51
B	1.5	38.1
C	0.5	12.7
D	.235	5.97

Notes:

- 1.molding material rated UL94V-0
- 2.max.lead temperature for soldering, 1/8" from body, 10seconds @260°C

ELECTRONIC DEVICES, INC. DESIGNERS AND MANUFACTURERS OF SOLID STATE DEVICES SINCE 1951.

21 GRAY OAKS AVENUE * YONKERS, NEW YORK 10710 914-965-4400 * FAX 914-965-5531 * 1-800-678-0828

e-mail:sales@edidiodes.com * website: <http://www.edidiodes.com>